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Tuning of Schottky barrier height of Al/n-Si by electron beam irradiation

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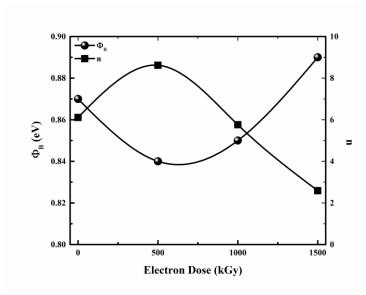
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Graphical abstract



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